

# NXL0840

SCR logic level

Rev. 01 — 26 February 2008

Product data sheet

## 1. Product profile

### 1.1 General description

Passivated sensitive gate Silicon-Controlled Rectifier (SCR) in a SOT54 plastic package

### 1.2 Features

- Direct interfacing to logic level ICs
- Direct interfacing to low-power gate drive circuits
- For operation on DC and rectified AC supplies

### 1.3 Applications

- Christmas lights control
- Protection and safety shutdown circuits e.g. lighting ballasts

### 1.4 Quick reference data

- $V_{\text{DRM}} \leq 400 \text{ V}$
- $I_{\text{T(RMS)}} \leq 0.8 \text{ A}$
- $I_{\text{TSM}} \leq 8 \text{ A (t = 10 ms)}$
- $I_{\text{T(AV)}} \leq 0.5 \text{ A}$

## 2. Pinning information

Table 1. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	anode (A)	<p>SOT54 (TO-92)</p>	<p>A — G — K sym037</p>
2	gate (G)		
3	cathode (K)		

### 3. Ordering information

**Table 2. Ordering information**

Type number	Package		Version
	Name	Description	
NXL0840	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54

### 4. Limiting values

**Table 3. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	400	V
$I_{T(AV)}$	average on-state current	half sine wave; $T_{lead} \leq 83\text{ °C}$ ; see <a href="#">Figure 1</a>	-	0.5	A
$I_{T(RMS)}$	RMS on-state current	all conduction angles; see <a href="#">Figure 4</a> and <a href="#">5</a>	-	0.8	A
$I_{TSM}$	non-repetitive peak on-state current	half sine wave; $T_j = 25\text{ °C}$ prior to surge; see <a href="#">Figure 2</a> and <a href="#">3</a>			
		$t = 10\text{ ms}$	-	8	A
		$t = 8.3\text{ ms}$	-	9	A
$I^2t$	$I^2t$ for fusing	$t_p = 10\text{ ms}$	-	0.32	A <sup>2</sup> s
$dl_T/dt$	rate of rise of on-state current	$I_{TM} = 2\text{ A}$ ; $I_G = 10\text{ mA}$ ; $dl_G/dt = 100\text{ mA}/\mu\text{s}$	-	50	A/ $\mu\text{s}$
$I_{GM}$	peak gate current		-	1	A
$V_{GM}$	peak gate voltage		-	5	V
$V_{RGM}$	peak reverse gate voltage		-	5	V
$P_{GM}$	peak gate power		-	2	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.1	W
$T_{stg}$	storage temperature		-40	+150	°C
$T_j$	junction temperature		-	125	°C

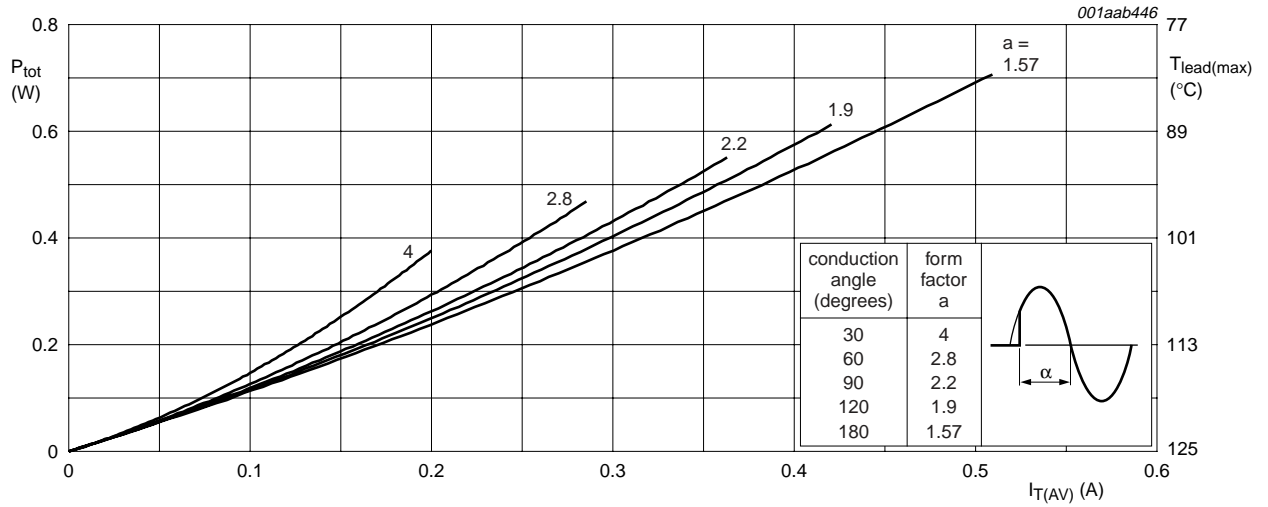


Fig 1. Total power dissipation as a function of average on-state current; maximum values

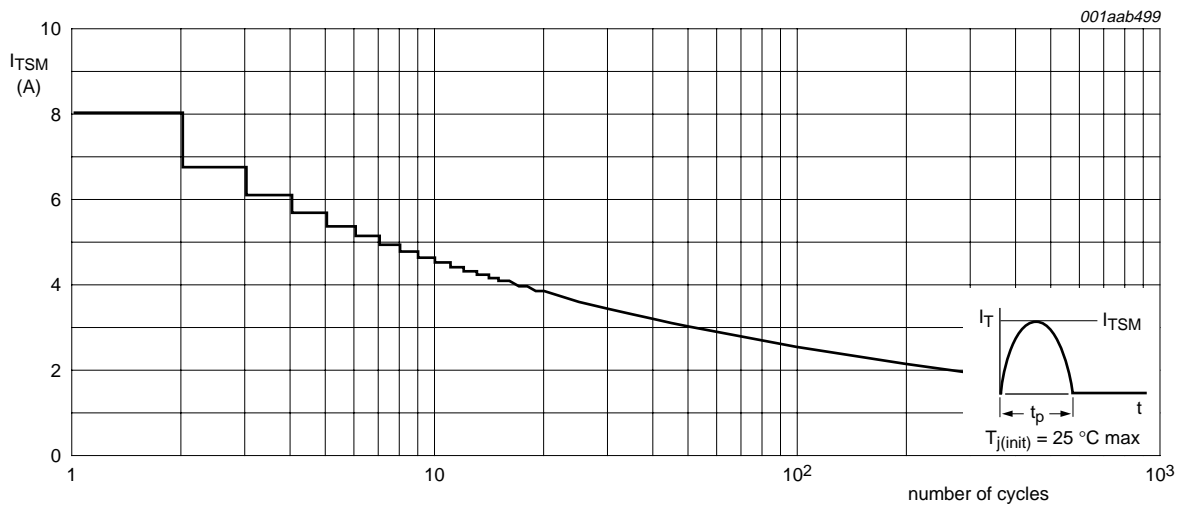
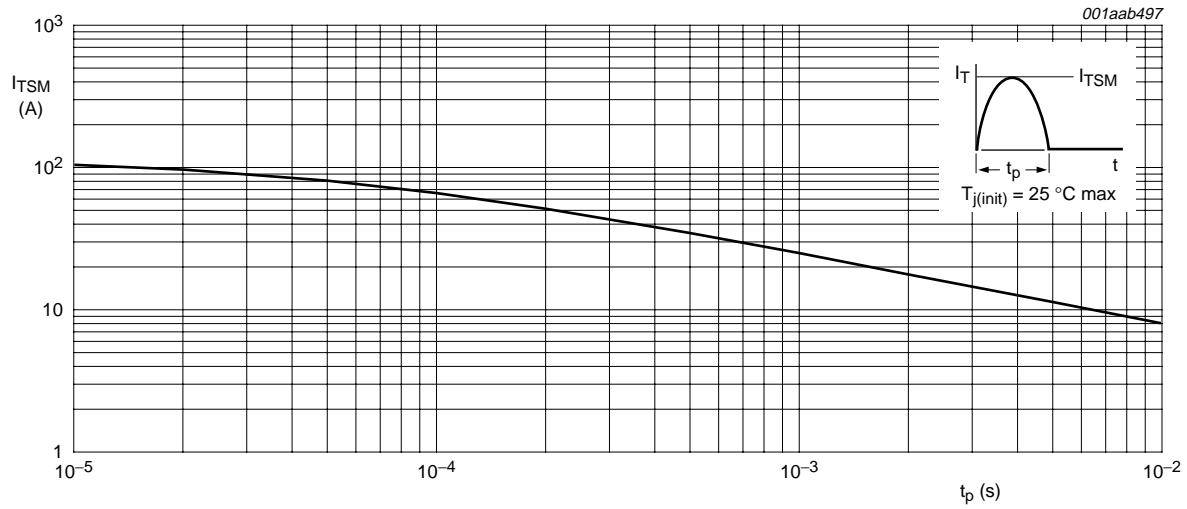
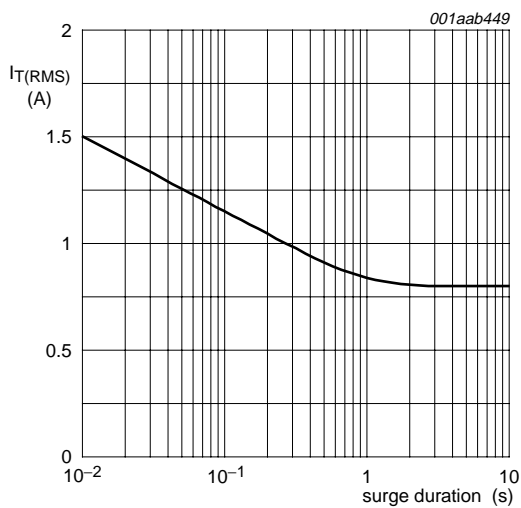


Fig 2. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



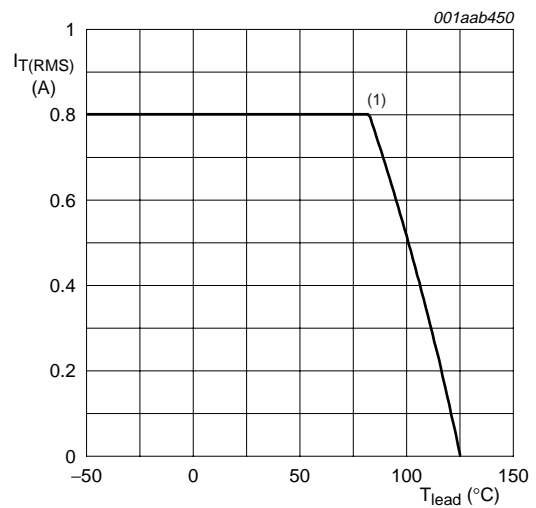
$t_p \leq 10\text{ ms}$

**Fig 3. Non-repetitive peak on-state current as a function of pulse width; maximum values**



$f = 50\text{ Hz}$   
 $T_{lead} = 83\text{ °C}$

**Fig 4. RMS on-state current as a function of surge duration; maximum values**



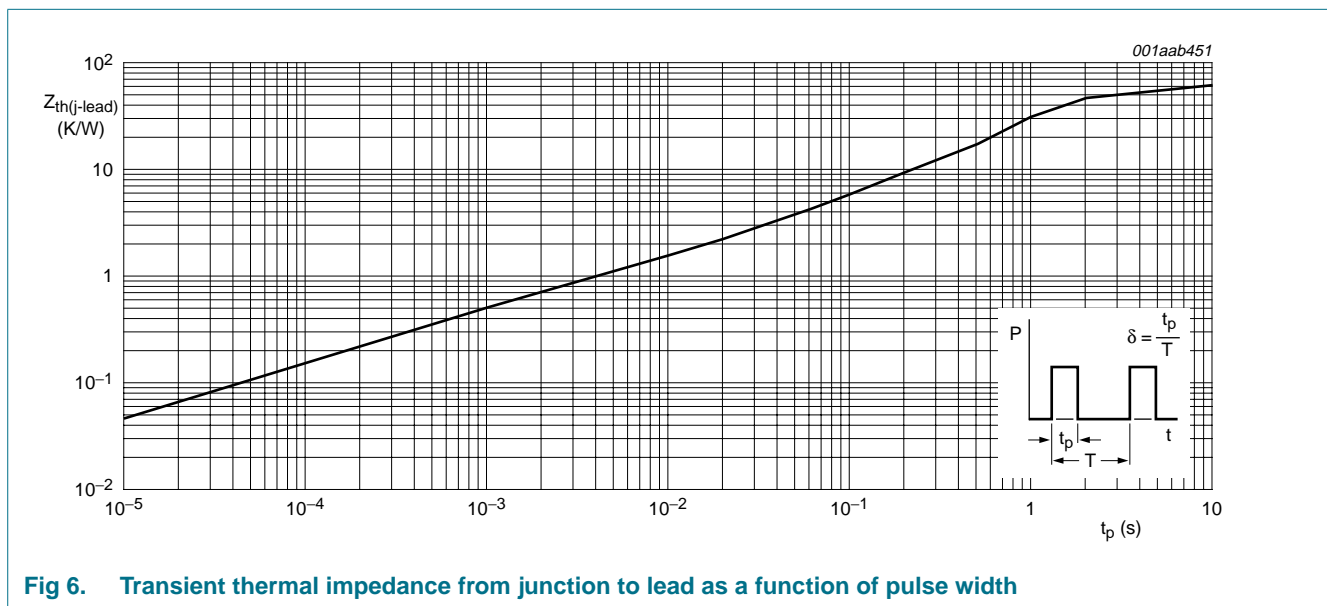
(1)  $T_{lead} = 83\text{ °C}$

**Fig 5. RMS on-state current as a function of lead temperature; maximum values**

## 5. Thermal characteristics

**Table 4. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-lead)}$	thermal resistance from junction to lead	see <a href="#">Figure 6</a>	-	-	60	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	printed circuit board mounted; lead length 4 mm	-	150	-	K/W

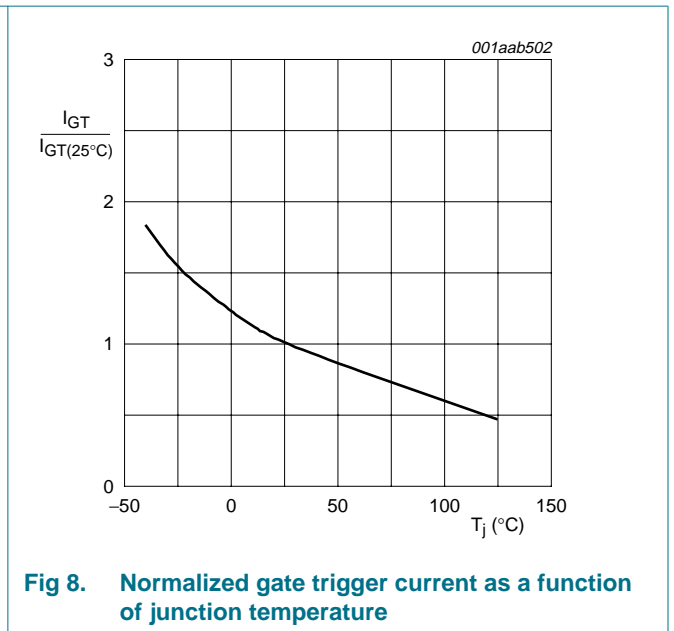
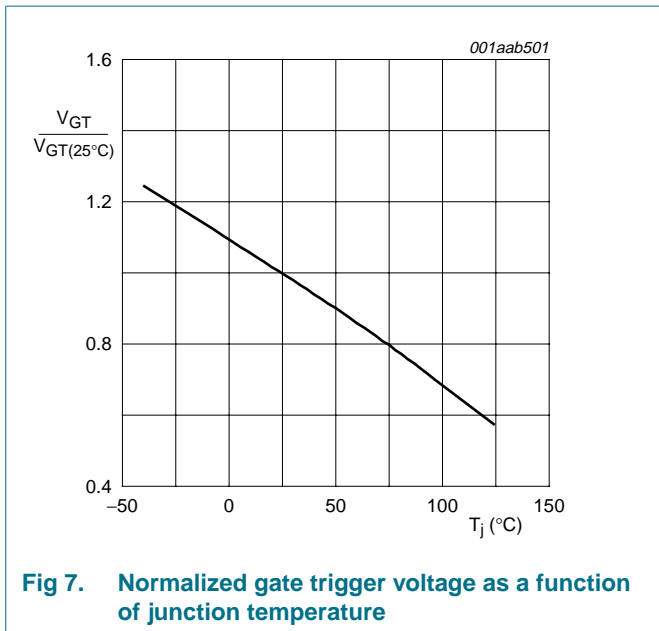


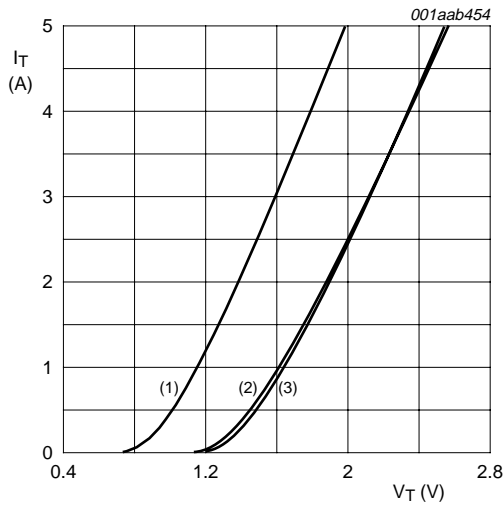
## 6. Characteristics

**Table 5. Characteristics**

$T_j = 25\text{ }^\circ\text{C}$  unless otherwise specified.

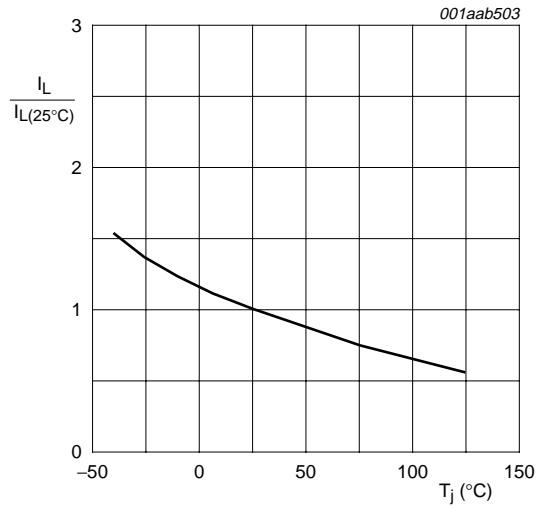
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 10\text{ mA}$ ; see <a href="#">Figure 8</a>	-	50	200	$\mu\text{A}$
$I_L$	latching current	$V_D = 12\text{ V}$ ; $I_G = 0.5\text{ mA}$ ; $R_{GK} = 1\text{ k}\Omega$ ; see <a href="#">Figure 10</a>	-	2	6	mA
$I_H$	holding current	$V_D = 12\text{ V}$ ; $I_G = 0.5\text{ mA}$ ; $R_{GK} = 1\text{ k}\Omega$ ; see <a href="#">Figure 11</a>	-	2	5	mA
$V_T$	on-state voltage	$I_T = 1.2\text{ A}$ ; see <a href="#">Figure 9</a>	-	1.25	1.7	V
$V_{GT}$	gate trigger voltage	$I_T = 10\text{ mA}$ ; see <a href="#">Figure 7</a>	-	-	-	-
		$V_D = 12\text{ V}$	-	0.5	0.8	V
		$V_D = V_{DRM(max)}$ ; $T_j = 125\text{ }^\circ\text{C}$	0.2	0.3	-	V
$I_D$	off-state current	$V_D = V_{DRM(max)}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; $R_{GK} = 1\text{ k}\Omega$	-	0.05	0.1	mA
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 0.67 \times V_{DRM(max)}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; exponential waveform; see <a href="#">Figure 12</a>	-	-	-	-
		$R_{GK} = 1\text{ k}\Omega$	200	600	-	V/ $\mu\text{s}$
		gate open circuit	-	25	-	V/ $\mu\text{s}$





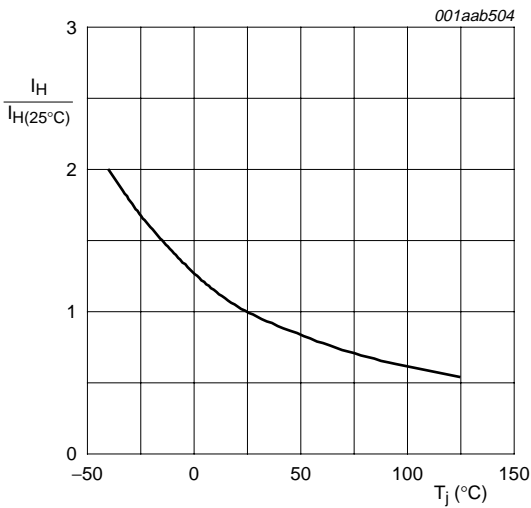
$V_o = 1.067\text{ V}$   
 $R_s = 0.187\ \Omega$   
 (1)  $T_j = 125\text{ }^\circ\text{C}$ ; typical values  
 (2)  $T_j = 125\text{ }^\circ\text{C}$ ; maximum values  
 (3)  $T_j = 25\text{ }^\circ\text{C}$ ; maximum values

**Fig 9. On-state current as a function of on-state voltage**



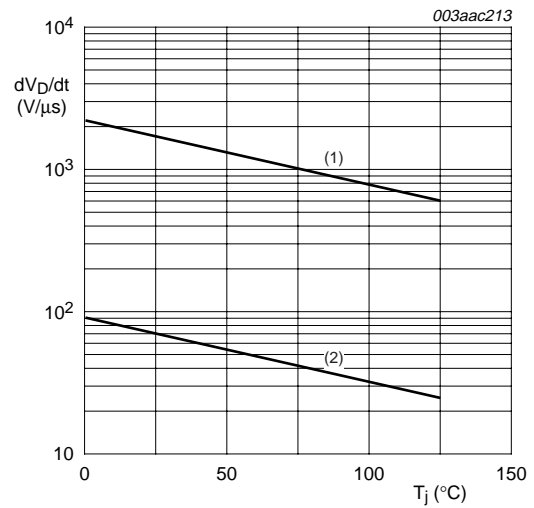
$R_{GK} = 1\text{ k}\Omega$

**Fig 10. Normalized latching current as a function of junction temperature**



$R_{GK} = 1\text{ k}\Omega$

**Fig 11. Normalized holding current as a function of junction temperature**



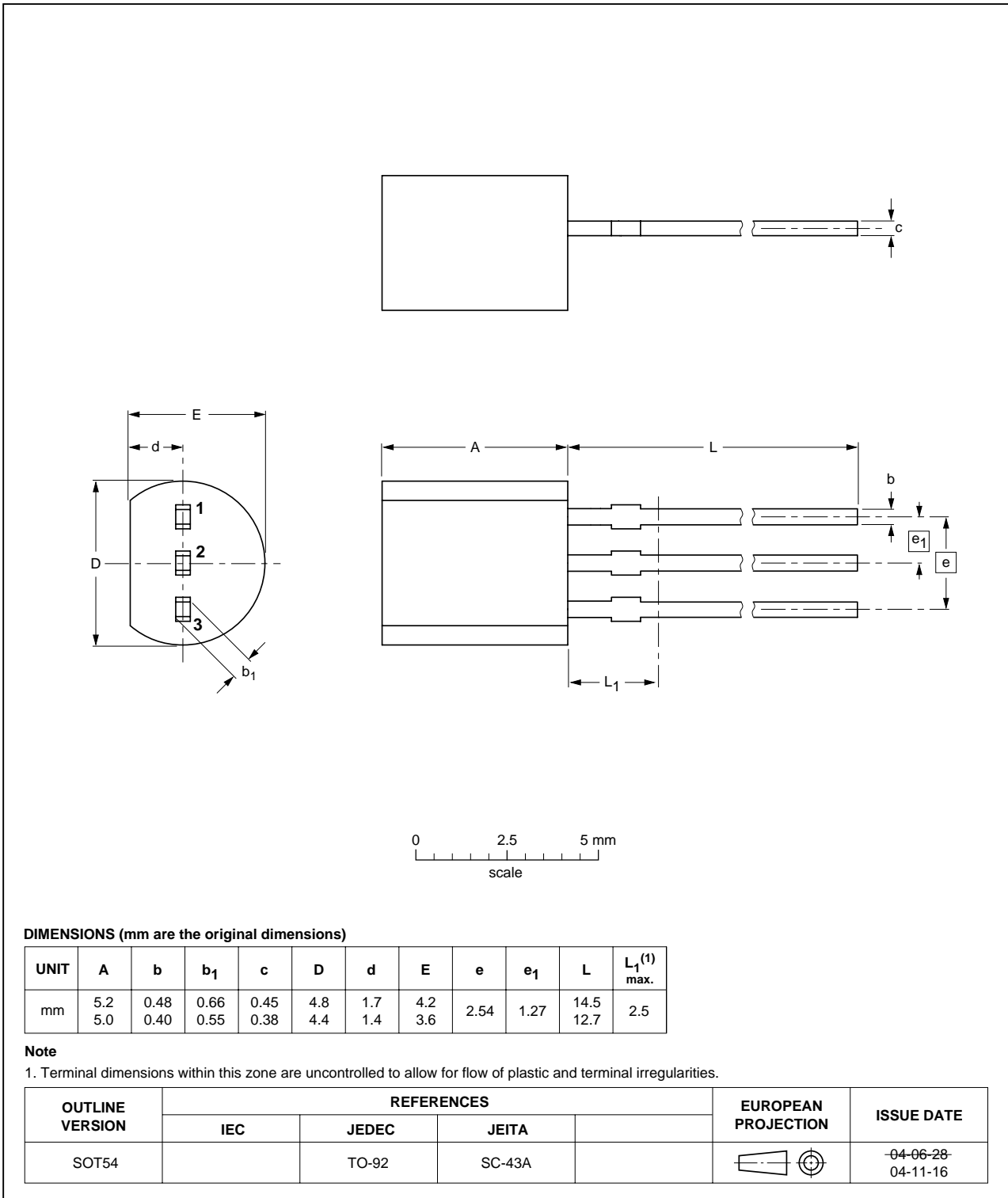
(1)  $R_{GK} = 1\text{ k}\Omega$   
 (2) Gate open-circuit

**Fig 12. Critical rate of rise of off-state voltage as a function of junction temperature; typical values**

**7. Package outline**

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



**Fig 13. Package outline SOT54 (TO-92)**



## 8. Revision history

Table 6. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
NXL0840_1	20080226	Product data sheet	-	-

## 9. Legal information

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Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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[2] The term 'short data sheet' is explained in section "Definitions".

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Date of release: 26 February 2008

Document identifier: NXL0840\_1